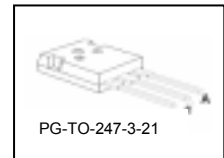


Fast Switching EmCon Diode

Features:

- 600 V EmCon technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage
- 175 °C junction operating temperature
- Easy paralleling
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models:
<http://www.infineon.com/emcon/>



Applications:

- Welding
- Motor drives

Type	V_{RRM}	I_F	$V_F, T_J=25^\circ\text{C}$	$T_{j,max}$	Marking	Package
IDW100E60	600V	100A	1.65V	175°C	D100E60	PG-TO-247-3-21

Maximum Ratings

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	600	V
Continuous forward current	I_F		A
$T_C = 25^\circ\text{C}$		150	
$T_C = 90^\circ\text{C}$		104	
$T_C = 100^\circ\text{C}$		96	
Surge non repetitive forward current	I_{FSM}	400	A
$T_C = 25^\circ\text{C}$, $t_p = 10$ ms, sine halfwave			
Maximum repetitive forward current	I_{FRM}	300	A
$T_C = 25^\circ\text{C}$, t_p limited by $t_{j,max}$, $D = 0.5$			
Power dissipation	P_{tot}		W
$T_C = 25^\circ\text{C}$		375	
$T_C = 90^\circ\text{C}$		212	
$T_C = 100^\circ\text{C}$		198	
Operating junction and storage temperature	T_j, T_{stg}	-55...+175	°C
Soldering temperature	T_S	260	°C
1.6mm (0.063 in.) from case for 10 s			

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
Thermal resistance, junction – case	R_{thJC}		0.40	K/W
Thermal resistance, junction – ambient	R_{thJA}		40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

Static Characteristic

Collector-emitter breakdown voltage	V_{RRM}	$I_R=0.25\text{mA}$	600	-	-	V
Diode forward voltage	V_F	$I_F=100\text{A}$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	1.65	2.0	
Reverse leakage current	I_R	$V_R=600\text{V}$ $T_j=25^\circ\text{C}$ $T_j=175^\circ\text{C}$	-	-	40	μA
			-	-	1000	

Dynamic Electrical Characteristics

Diode reverse recovery time	t_{rr}	$T_j=25^\circ\text{C}$	-	120	-	ns
Diode reverse recovery charge	Q_{rr}	$V_R=400\text{V}$,	-	3.6	-	μC
Diode peak reverse recovery current	I_{rr}	$I_F=100\text{A}$,	-	49.5	-	A
Diode peak rate of fall of reverse recovery current during t_b	dl_{rr}/dt	$dl_F/dt=1200\text{A}/\mu\text{s}$	-	750	-	$\text{A}/\mu\text{s}$

Diode reverse recovery time	t_{rr}	$T_j=125^\circ\text{C}$	-	168	-	ns
Diode reverse recovery charge	Q_{rrm}	$V_R=400\text{V}$,	-	5.8	-	μC
Diode peak reverse recovery current	I_{rr}	$I_F=100\text{A}$,	-	61.6	-	A
Diode peak rate of fall of reverse recovery current during t_b	dl_{rr}/dt	$dl_F/dt=1200\text{A}/\mu\text{s}$	-	705	-	$\text{A}/\mu\text{s}$

Diode reverse recovery time	t_{rr}	$T_j=175^\circ\text{C}$	-	200	-	ns
Diode reverse recovery charge	Q_{rrm}	$V_R=400\text{V}$,	-	7.8	-	μC
Diode peak reverse recovery current	I_{rr}	$I_F=100\text{A}$,	-	67.0	-	A
Diode peak rate of fall of reverse recovery current during t_b	dl_{rr}/dt	$dl_F/dt=1200\text{A}/\mu\text{s}$	-	650	-	$\text{A}/\mu\text{s}$

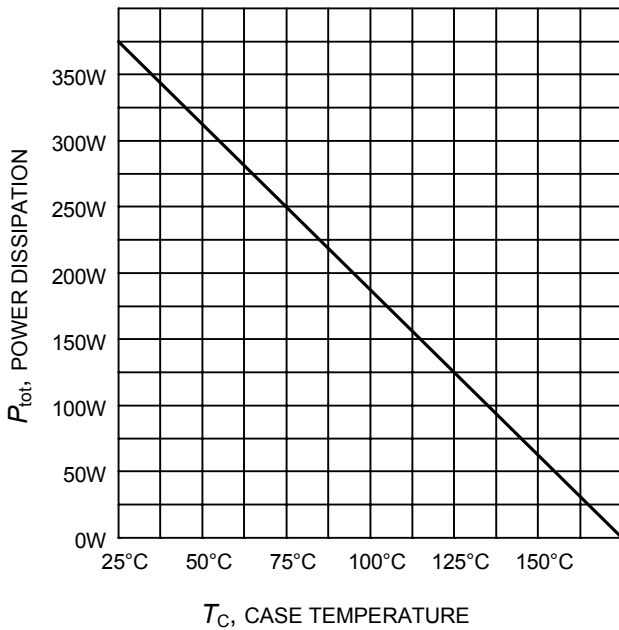


Figure 1. Power dissipation as a function of case temperature
($T_j \leq 175^\circ\text{C}$)

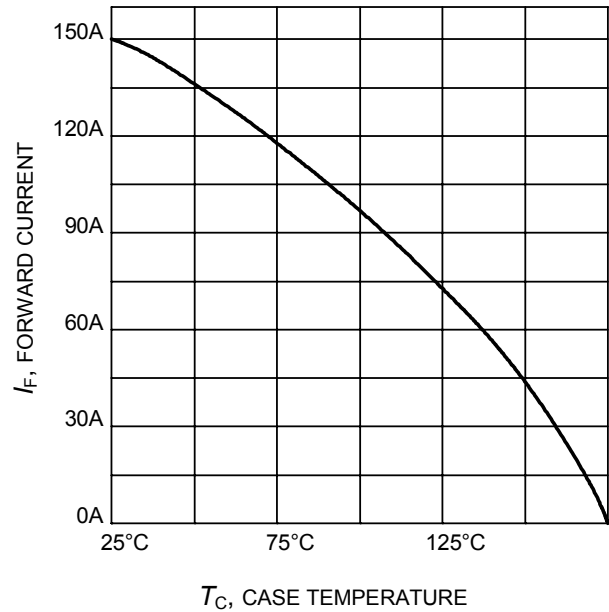


Figure 2. Diode forward current as a function of case temperature
($T_j \leq 175^\circ\text{C}$)

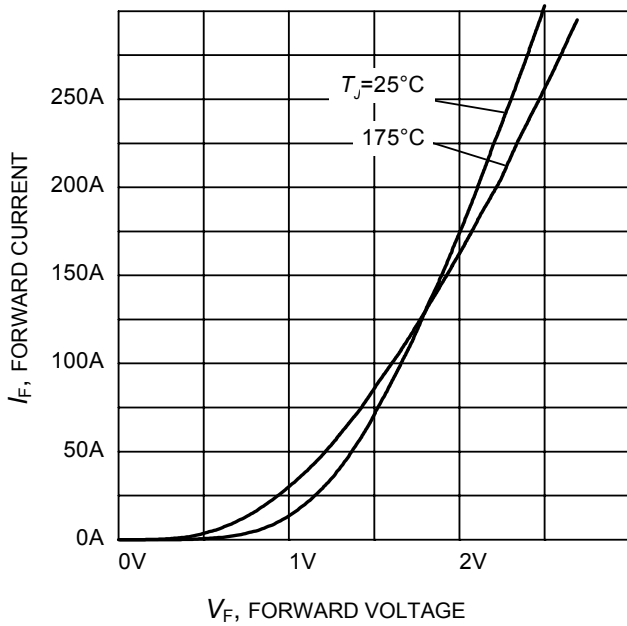


Figure 3. Typical diode forward current as a function of forward voltage

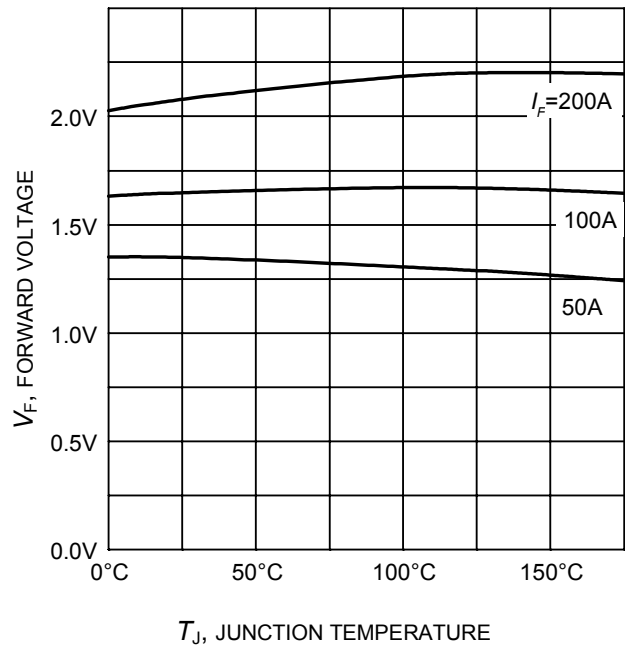
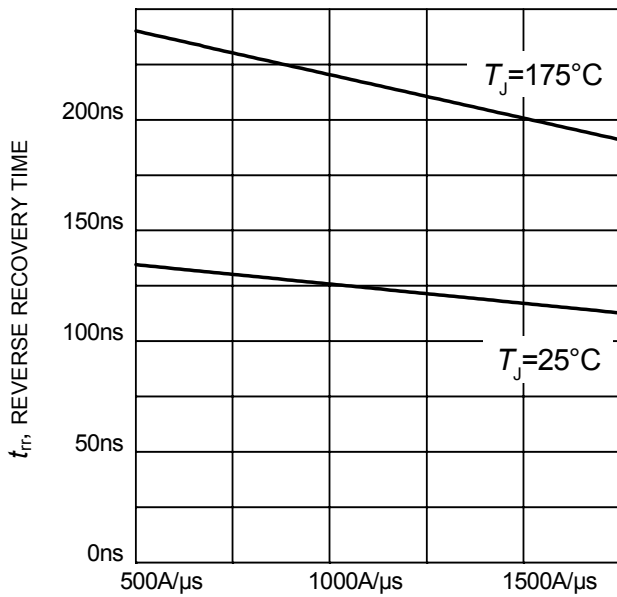
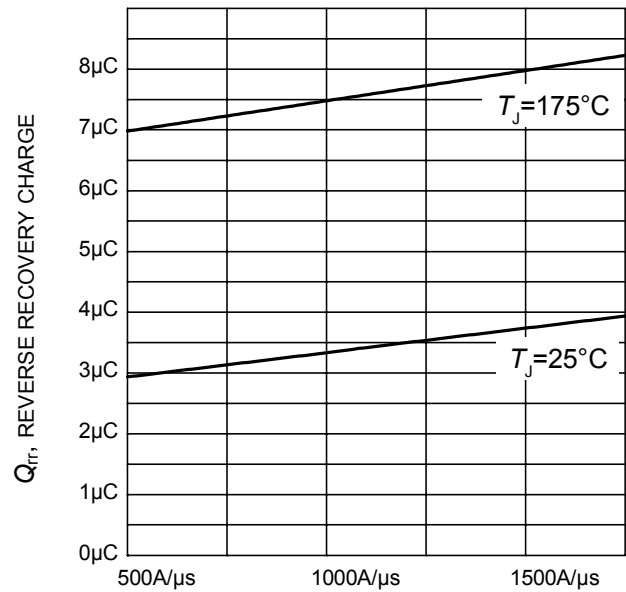


Figure 4. Typical diode forward voltage as a function of junction temperature



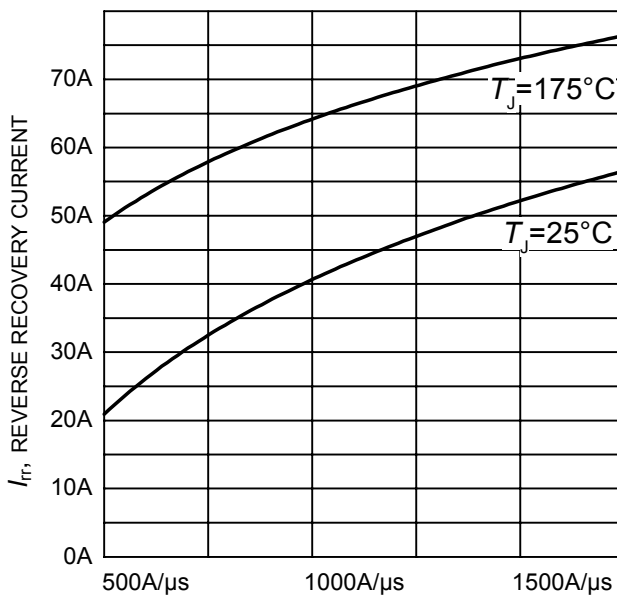
di_F/dt , DIODE CURRENT SLOPE

Figure 5. Typical reverse recovery time as a function of diode current slope
 ($V_R=400V$, $I_F=100A$,
 Dynamic test circuit in Figure E)



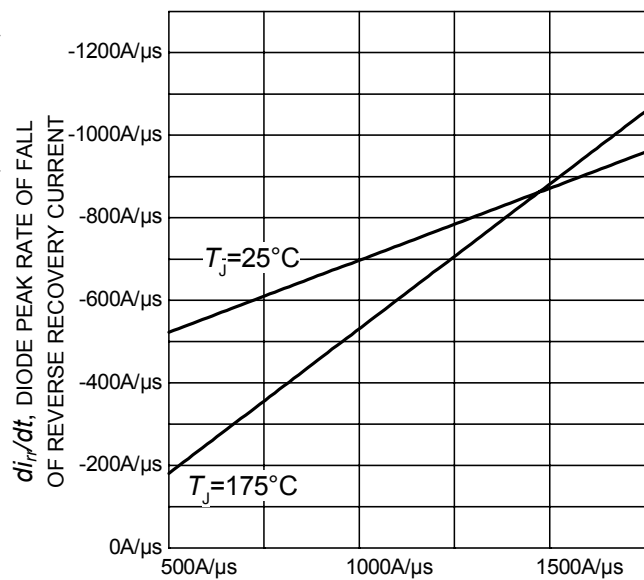
di_F/dt , DIODE CURRENT SLOPE

Figure 6. Typical reverse recovery charge as a function of diode current slope
 ($V_R = 400V$, $I_F = 100A$,
 Dynamic test circuit in Figure E)



di_F/dt , DIODE CURRENT SLOPE

Figure 7. Typical reverse recovery current as a function of diode current slope
 ($V_R = 400V$, $I_F = 100A$,
 Dynamic test circuit in Figure E)



di_F/dt , DIODE CURRENT SLOPE

Figure 8. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope
 ($V_R=400V$, $I_F=100A$,
 Dynamic test circuit in Figure E)

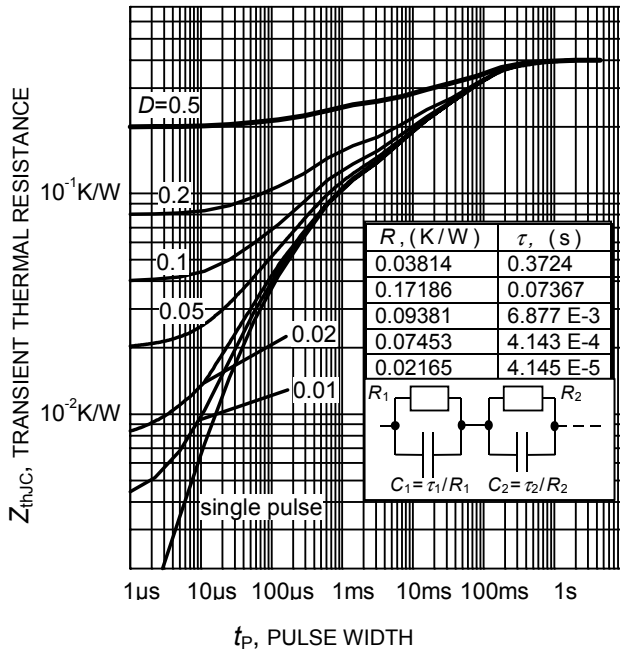
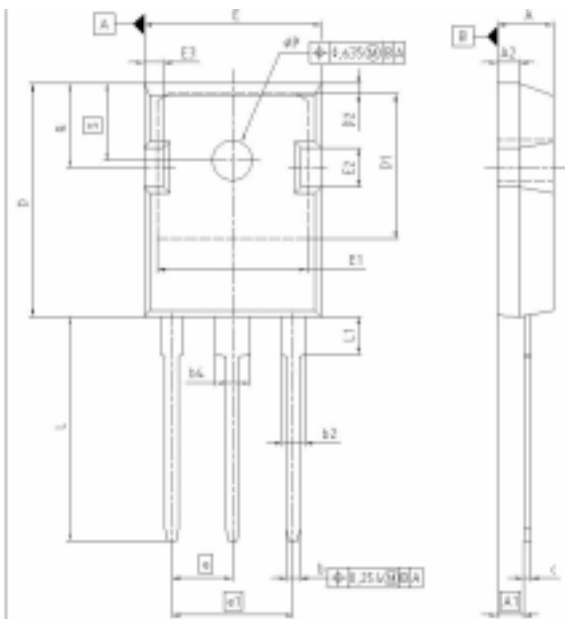


Figure 9. Diode transient thermal impedance as a function of pulse width
($D=t_p/T$)

PG-TO247-3-21



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.905	5.157	0.193	0.203
A1	2.273	2.527	0.090	0.099
A2	1.653	2.107	0.075	0.083
b	1.073	1.327	0.047	0.052
b2	1.903	2.306	0.075	0.091
b4	2.870	3.454	0.113	0.136
c	0.549	0.752	0.024	0.030
D	29.823	24.077	0.820	0.890
D1	17.323	17.831	0.682	0.702
D2	1.083	1.317	0.042	0.052
E	15.773	16.827	0.621	0.661
E1	13.893	14.847	0.547	0.587
E2	3.683	3.107	0.145	0.122
E3	1.663	1.997	0.065	0.078
e	5.450		0.215	
et	10.900		0.430	
N	3		3	
L	20.053	20.307	0.789	0.799
L1	4.166	4.472	0.164	0.175
ap	3.559	3.661	0.140	0.144
Q	5.490	5.747	0.216	0.228
S	6.043	6.297	0.238	0.248

**Published by
Infineon Technologies AG,
Bereich Kommunikation
Am Campeon 1-12,
D-85579 Neubiberg
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